

PATENT ASSIGNMENT COVER SHEET

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SUBMISSION TYPE:	NEW ASSIGNMENT
NATURE OF CONVEYANCE:	ASSIGNMENT
CONVEYING PARTY DATA	
Name	Execution Date
LG ELECTRONICS, INC.	09/04/2013
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Name:	LG INNOTEK CO. LTD.
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PROPERTY NUMBERS Total: 1	
Property Type	Number
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NAME OF SUBMITTER:	RANDALL C. PYLES
Signature:	/RANDALL C. PYLES, #66,523/
Date:	12/05/2013

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Total Attachments: 5

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PATENT ASSIGNMENT AGREEMENT

WHEREAS, LG Electronics, Inc., having a place of business at 20, Yeouido-dong, Yeongdeungpo-gu, Seoul 150-721, Republic of Korea (hereinafter "Assignor") is the sole and exclusive owner of certain United States and/or foreign patents and/or patent applications listed in Schedule A annexed hereto (collectively referred to as the "Patents"); and

WHEREAS LG Innotek Co. Ltd., a Korean Corporation having a place of business at Seoul Square 20F, Namdaemunno 5-ga, Jung-gu, Seoul 100-174, Republic of Korea (hereinafter "Assignee") is desirous of acquiring the right, title and interest in, to and under the said Patents (and all foreign counterparts and related foreign patents).

Now, Therefore,

For good and valuable consideration, the receipt of which is hereby acknowledged, Assignor does hereby sell, assign, transfer and set over to Assignee, subject to existing encumbrances, the Patents listed in Schedule A, and any inventions claimed in said Patent, any reissue or reissues of said Patents already granted and which may be granted, any divisionals, continuations, continuations-in-part, substitutions, certificates of reexamination already granted and which may be granted the same to be held and enjoyed by Assignee for its own use and enjoyment, and for the use and enjoyment of its successors, assigns or other legal representatives, to the end of the term or terms for which said Patents are or may be granted, reissued or extended as fully and entirely as the same would have been held and enjoyed by Assignor, if this assignment and sale had not been made; together with all claims for damages, royalties, or injunctive relief by reason of past, current, and future infringement and/or provisional rights under said Patents, with the right to sue for, and collect or obtain the same for its own use and behalf, and for the use and behalf of its successors, assigns or other legal representatives.

And, Assignor, hereby authorizes and requests the Commissioner of Patents and Trademarks to issue any and all Letters Patents of the United States on said inventions to Assignee as assignee of the entire interest.

Assignor and Assignee have executed this Patent Assignment Agreement by their duly authorized representatives.

Assignor:

LG Electronics, Inc.

By: 

Name: DONG SUK BAE

Title: Senior Manager

Date: 2013. 09. 04

Assignee:

LG Innotek Co., Ltd.

By: 

Name: Gyung Rae Kim

Title: Senior Manager

Date: September 16, 2013

Schedule A

Application No.	Filing Date	Patent No.	Issue Date	L.G. Ref.	Docket No.	LGIT REF	Title
09/905,969	2001/07/17	7,067,849	2006/06/27	05ORIOLO1US02	10401.004.00	P2013-00001US	DIODE HAVING HIGH BRIGHTNESS AND METHOD THEREOF
09/982,980	2001/10/22	6,949,395	2005/09/27	05ORIOLO5US02	10401.008.00	P2013-00005US	METHOD OF MAKING DIODE HAVING REFLECTIVE LAYER
09/983,994	2001/10/26	7,148,520	2006/12/12	05ORIOLO2US02	10401.005.00	P2013-00002US	DIODE HAVING VERTICAL STRUCTURE AND METHOD OF MANUFACTURING THE SAME
10/103,523	2002/03/22	7,214,325	2007/05/08	05ORIOLO6US02	10401.009.00	P2013-00006USP1	METHOD OF FABRICATING OHMIC CONTACT ON N-TYPE GALLIUM NITRIDE (GaN) OF ROOM TEMPERATURE BY PLASMA SURFACE TREATMENT
10/118,316	2002/04/09	Abandoned	---	05ORIOLO8US02	10401.011.00	P2013-00008US	METHOD OF FABRICATING VERTICAL STRUCTURE LEDS
10/118,317	2002/04/09	8,294,172	2012/10/23	05ORIOLO7US02	10401.010.00	P2013-00007US	METHOD OF FABRICATING VERTICAL DEVICES USING A METAL SUPPORT FILM
10/118,318	2002/04/09	6,818,532	2004/11/16	05ORIOLO3US02	10401.006.00	P2013-00003US	METHOD OF ETCHING SUBSTRATES
10/179,010	2002/06/26	6,841,802	2005/01/11	05ORIOLO4US01	10401.007.00	P2013-00004US	THIN FILM LIGHT EMITTING DIODE
10/316,004	2002/12/11	6,744,196	2004/06/01	05ORIOLO9US01	10401.012.00	P2013-00009US	THIN FILM LED
10/795,287	2004/03/09	7,420,217	2008/09/02	05ORIOLO9US02 C1	10401.012.20	P2013-00009USC1	THIN FILM LED
10/928,202	2004/08/30	7,012,012	2006/03/14	05ORIOLO3US06 C1	10401.006.20	P2013-00003USC1	METHOD OF ETCHING SUBSTRATES
10/975,095	2004/10/28	7691,650	2010/04/06	05ORIOLO4US04 C1	10401.007.10	P2013-00004USD1	THIN FILM LIGHT EMITTING DIODE
11/002,413	2004/12/03	7,569,865	2009/08/04	05ORIOLO8US07 C2	10401.011.10	P2013-00008USD1	METHOD OF FABRICATING VERTICAL STRUCTURE LEDS
11/030,323	2005/01/07	7,588,952	2009/09/15	05ORIOLO8US08 C2	10401.011.20	P2013-00008USC1	METHOD OF FABRICATING VERTICAL STRUCTURE LEDS
11/203,322	2005/08/15	7,682,854	2010/03/23	05ORIOLO5US06 C1	10401.008.20	P2013-00005USC1	METHOD OF MAKING DIODE HAVING REFLECTIVE LAYER

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11/232,956	2005/09/23	7,250,638	2007/07/31	05OR10L08US09 C3	10401.011.22	P2013-00008USC2	METHOD OF FABRICATING VERTICAL STRUCTURE LEDS
11/232,957	2005/09/23	7,563,629	2009/07/21	05OR10L08US10 C4	10401.011.21	P2013-00008USC3	METHOD OF FABRICATING VERTICAL STRUCTURE LEDS
11/247,225	2005/10/12	7,582,912	2009/09/01	05OR10L01US02 C1	10401.004.10	P2013-00001USC1	DIODE HAVING HIGH BRIGHTNESS AND METHOD THEREOF
11/298,507	2005/12/12	7,371,597	2008/05/13	05OR10L02US02 D1	10401.005.10	P2013-00002USD1	DIODE HAVING VERTICAL STRUCTURE AND METHOD OF MANUFACTURING THE SAME
11/311,230	2005/12/20	7,294,521	2007/11/13	05OR10L07US06 C1	10401.010.10	P2013-00007USD1	METHOD OF FABRICATING VERTICAL DEVICES USING A METAL SUPPORT FILM
11/311,229	2005/12/20	8,022,386	2011/09/20	05OR10L07US07 C2	10401.010.11	P2013-00007USD2	VERTICAL TOPOLOGY LIGHT EMITTING DEVICE
11/497,268	2006/08/02	8,368,115	2013/02/05	05OR10L07US02 D3	10401.010.20	P2013-00007USC1	METHOD OF FABRICATING VERTICAL DEVICES USING A METAL SUPPORT FILM
11/544,645	2006/10/10	7,414,271	2008/08/19	05OR10L09US02 C1D1	10401.012.21	P2013-00009USD1	THIN FILM LED
11/593,470	2006/11/07	7,821,021	2010/10/26	05OR10L02US02 C2	10401.005.20	P2013-00002USC1	DIODE HAVING VERTICAL STRUCTURE AND METHOD OF MANUFACTURING THE SAME
11/713,045	2007/03/02	7,785,908	2010/08/31	05OR10L05US02 C2	10401.008.21	P2013-00005USC2	METHOD OF MAKING DIODE HAVING REFLECTIVE LAYER
11/882,575	2007/08/02	7,772,020	2010/08/10	05OR10L07US02 C3	10401.010.21	P2013-00007USC2	METHOD OF FABRICATING VERTICAL DEVICES USING A METAL SUPPORT FILM
11/896,307	2007/08/30	7,462,881	2008/12/09	05OR10L08US02 C6	10401.011.23	P2013-00008USC4	METHOD OF FABRICATING VERTICAL STRUCTURE LEDS
11/896,772	2007/09/05	7,576,368	2009/08/18	05OR10L08US02 C5	10401.011.24	P2013-00008USC5	METHOD OF FABRICATING VERTICAL STRUCTURE LEDS
11/978,680	2007/10/30	7,649,210	2010/01/19	05OR10L04US01 C2	10401.007.20	P2013-00004USC1	THIN FILM LIGHT EMITTING DIODE
12/285,557	2008/10/08	8,106,417	2012/01/31	05OR10L07US02 D4	10401.010.22	P2013-00007USC3	A VERTICAL TOPOLOGY LIGHT EMITTING DEVICE USING A CONDUCTIVE SUPPORT STRUCTURE
12/458,703	2009/07/21	7,816,705	2010/10/19	05OR10L08US07 C2C1	10401.011.25	P2013-00008USC6	METHOD OF FABRICATING VERTICAL STRUCTURE LEDS
12/461,681	2009/08/20	7,939,849	2011/05/10	05OR10L01US02 C1C1	10401.004.20	P2013-00001USC2	DIODE HAVING HIGH BRIGHTNESS AND METHOD THEREOF

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Application No.	Filing Date	Patent No.	Issue Date	LG Ref.	Docket No.	LGIT REF	Title
12/591,164	2009/11/10	8,384,091	2013/02/26	05OR10L04US01 C2C2	10401.007.22	P2013-00004USC2	THIN FILM LIGHT EMITTING DIODE
12/591,165	2009/11/10	8,445,921	2013/05/21	05OR10L04US01 C2C1	10401.007.21	P2013-00004USC3	THIN FILM LIGHT EMITTING DIODE
12/654,894	2010/01/07	7,863,638	2011/01/04	05OR10L02US02 C2C1	10401.005.21	P2013-00002USC2	DIODE HAVING VERTICAL STRUCTURE AND METHOD OF MANUFACTURING THE SAME
12/654,988	2010/01/12	8,288,787	2012/10/16	05OR10L04US01 C2C3	10401.007.24	P2013-00004USC4	THIN FILM LIGHT EMITTING DIODE
12/654,992	2010/01/12	7,956,364	2011/06/07	05OR10L04US01 C2C4	10401.007.23	P2013-00004USC5	THIN FILM LIGHT EMITTING DIODE
12/797,335	2010/06/09	7,928,465	2011/04/19	05OR10L08US07 C2C1C1	10401.011.26	P2013-00008USC7	METHOD OF FABRICATING VERTICAL STRUCTURE LEDS
12/840,840	2010/07/21	7,915,632	2011/03/29	05OR10L02US02 C2C2	10401.005.22	P2013-00002USC3	DIODE HAVING VERTICAL STRUCTURE AND METHOD OF MANUFACTURING THE SAME
12/841,674	2010/07/22	8,236,585	2012/08/07	05OR10L05US02 C2C1	10401.008.22	P2013-00005USC3	METHOD OF MAKING DIODE HAVING REFLECTIVE LAYER
12/941,627	2010/11/08	8,008,681	2011/08/30	05OR10L02US02 C2C2C1	10401.005.23	P2013-00002USC4	DIODE HAVING VERTICAL STRUCTURE AND METHOD OF MANUFACTURING THE SAME
13/047,371	2011/03/14	8,384,120	2013/02/26	05OR10L08US07 C2C1C1C1	10401.00011.U S2A	P2013-00008USC8	METHOD OF FABRICATING VERTICAL STRUCTURE LEDS
13/074,566	2011/03/29	Pending	---	05OR10L01US02 C1C1D1	10401.00004.U S14	P2013-00001USD1	DIODE HAVING HIGH BRIGHTNESS AND METHOD THEREOF
13/110,545	2011/05/18	8,207,552	2012/06/26	05OR10L04US01 C2C4C1	10401.00007.U S27	P2013-00004USC6	THIN FILM LIGHT EMITTING DIODE
13/216,531	2011/08/24	8,519,421	2013/08/27	05OR10L02US02 C2C2C1C1	10401.00005.U S26	P2013-00002USC5	DIODE HAVING VERTICAL STRUCTURE AND METHOD OF MANUFACTURING THE SAME
13/550,097	2012/07/16	Pending	---	05OR10L05US02 C2C1C1	10401.00008.U S23	P2013-00005USC4	METHOD OF MAKING DIODE HAVING REFLECTIVE LAYER
13/678,333	2012/11/15	Pending	---	05OR10L07US02 D3C1	10401.00010.U S23	P2013-00007USC4	VERTICAL TOPOLOGY LIGHT EMITTING DEVICE
13/750,376	2013/01/25	Pending	---	05OR10L08US07 C2C1C1C1C1	10401.00011.U S27	P2013-00008USC9	METHOD OF FABRICATING VERTICAL STRUCTURE LEDS

Application No.	Filing Date	Patent No.	Issue Date	LG Ref.	Docket No.	LGIT REF	Title
13/855,637	2013/04/02	Pending	---	05ORIOLO4US01 C2C1C1	10401.00007.U S25	P2013-00004USC7	THIN FILM LIGHT EMITTING DIODE
13/934,852	2013/07/03	Pending	---	05ORIOLO7US02 D3C1C1	10401.00010.U S24	P2013-00007USC5	VERTICAL TOPOLOGY LIGHT EMITTING DEVICE
13/951,344	2013/07/25	Pending	---	05ORIOLO2US02 C2C2C1C1C1	10401.00005.U S27	P2013-00002USC6	DIODE HAVING VERTICAL STRUCTURE

And any and all related extensions, divisionals, continuations, continuations-in-part, reissues, reexaminations, substitutions, and foreign counterparts of the foregoing.

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